

## **isc** Silicon NPN Power Transistor

# 2SD866

#### DESCRIPTION · Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 80V(Min) Good Linearity of h<sub>FE</sub> · Low Collector Saturation Voltage PIN 1. BASE 2.COLLECTOR : V<sub>CE(sat)</sub>= 0.5V(Max)@I<sub>C</sub>= 5A 3. BMITTER · Minimum Lot-to-Lot variations for robust device TO-220C package 123 performance and reliable operation **APPLICATIONS** -S · Designed for power switching applications. ABSOLUTE MAXIMUM RATINGS(Ta=25℃) SYMBOL PARAMETER VALUE UNIT Vсво Collector-Base Voltage 130 V $V_{\text{CEO}}$ Collector-Emitter Voltage 80 V С Emitter-Base Voltage V $V_{\text{EBO}}$ 7 mm DIM MIN MAX **Collector Current-Continuous** 7 lc А 15.50 15.90 A В 9.80 10.20 4.20 С 4.50 **Collector Current-Peak** 15 А Ісм D 0.70 0.90 3.70 5.18 F 3.40 G 4.98 **Collector Power Dissipation** 40 W Pc 2.90 Н 2.68 @ Tc=25°C 1 0.44 0.60 Κ 12.80 13.40 °C 1.20 ТJ Junction Temperature 150 1.45 Q 2.70 2.90 2.30 R 2.70 1.29 -55~150 °C S 1.35 Storage Temperature Range Tstg U 6.65 6.45 ٧ 8.66 8.86

isc website: <u>www.iscsemi.com</u>



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#### **ELECTRICAL CHARACTERISTICS**

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.25A			0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.25A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			10	uA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	uA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 2V	45			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 2V	60		260	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		30		MHz

#### Switching Times

ton	Turn-On Time		0.5	μ <b>S</b>
ts	Storage Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = I <sub>B2</sub> = 0.2A	1.5	μs
t <sub>f</sub>	Fall Time		0.1	μs

#### h<sub>FE-2</sub> Classifications

R	Q	Р
60-120	90-180	130-260

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